

2MBI1200U4G-120

IGBT Modules

IGBT MODULE (U series) 1200V / 1200A / 2 in one package

Features

High speed switching Voltage drive Low Inductance module structure

Applications

Inverter for Motor Drive AC and DC Servo Drive Amplifier Uninterruptible Power Supply Industrial machines, such as Welding machines



Maximum Ratings and Characteristics

■ Absolute Maximum Ratings (at Tc=25°C unless otherwise specified)

Items	Symbols	Conditions		Maximum ratings	Units	
Collector-Emitter voltage	Vces			1200		
Gate-Emitter voltage	Vges			±20	V	
	lo.	Continuous	Tc=25°C	1600		
	Ic	Continuous	Tc=80°C	1200		
Collector current	la pulas	1ma	Tc=25°C	3200	٨	
Collector current	Ic pulse	1ms	Tc=80°C	2400	Α	
	-lc			1200		
	-lc pulse	1ms		2400		
Collector power dissipation	Pc	1 device		6250	W	
Junction temperature	Tj			150	°C	
Storage temperature	Tstg			-40 ~ +125		
Isolation voltage Between terminal and copp	er base (*1) Viso	AC: 1min.		4000	VAC	
Mounting (*2)	M6					
Screw torque Terminals (*3)	M8			10	N m	
Terminais (3)	M4			2.5		

Note *1: All terminals should be connected together when isolation test will be done.

Note *2: Recommendable Value: Mounting 4.25~5.75 Nm (M6)

Note *3: Recommendable Value: Main Terminals 8~10 Nm (M8)

Sense Terminals 1.7~2.5 Nm (M4)

● Electrical characteristics (at Tj= 25°C unless otherwise specified)

lama	Symbolo	Symbols Conditions		Characteristics			Units
Items	Symbols			min.	typ.	max.	Units
Zero gate voltage collector current	Ices	$V_{GE} = 0V, V_{CE} = 1200V$		-	-	1.0	mA
Gate-Emitter leakage current	Iges	$V_{CE} = 0V$, $V_{GE} = \pm 20V$		-	-	1600	nA
Gate-Emitter threshold voltage	V _{GE (th)}	V _{CE} = 20V, I _C = 1200mA		5.5	6.5	7.5	V
Collector-Emitter saturation voltage	V _{CE} (sat)		Tj=25°C	-	2.22	2.41	V
	(main terminal)	V _{GE} = 15V	Tj=125°C	-	2.42	-	
	V _{CE} (sat)	I _c = 1200A	Tj=25°C	-	1.90	2.05	
	(chip)		Tj=125°C	-	2.10	-	
Input capacitance	Cies	V _{CE} = 10V, V _{GE} = 0V, f = 1MHz		-	135	-	nF
Turn-on	ton	$V_{cc} = 600V$ $R_{con} = 3.3\Omega$ $R_{con} = 1200A$ $R_{con} = 0.82\Omega$		-	1.35	-	
	tr			-	0.65	-	
Turn-off	toff	V _{GE} = ±15V		-	0.80	-	μs
	tf	Tj = 125°C		-	0.20	-	
Forward on voltage	V _F		Tj=25°C	-	1.97	2.16	V
	(main terminal)) V _{GE} = 0V I _F = 1200A	Tj=125°C	-	2.07	-	
	VF		Tj=25°C	-	1.65	1.80	
	(chip)		Tj=125°C	-	1.75	-	
Reverse recovery	trr	I _F = 1200A		-	0.45	-	μs
Lead resistance, terminal-chip	R lead			-	0.27	3450	mΩ

Thermal resistance characteristics

Items	Symbols	Conditions	Characteristics			Units	
items		Conditions	min.	typ.	max.	Ullits	
Thermal resistance (1device)	Rth(j-c)	IGBT	-	-	0.020		
		FWD	-	-	0.033	°C/W	
Contact thermal resistance (1device)	Rth(c-f)	with Thermal Compound (*4)	-	0.006	-		

Note *4: This is the value which is defined mounting on the additional cooling fin with thermal compound.

Collector current : Ic[A]

400

0

0.0

1.0

■ Characteristics (Representative)

Tj=25°C,chip 2800 VgE=20V 12V 15V 2400 2000 1600 10V 1200 800

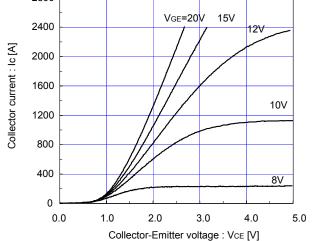
2.0

Collector-Emitter voltage: VcE [V]

Collector current vs. Collector-Emitter voltage (typ.)

Tj= 125°C, chip 2800 Vge=20V 15V 2400 2000

Collector current vs. Collector-Emitter voltage (typ.)



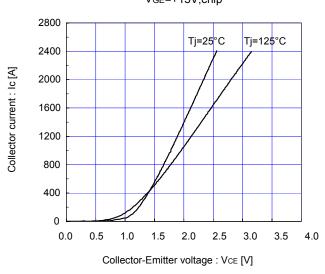
Collector-Emitter voltage vs. Gate-Emitter voltage (typ.) V_{GE}=+15V,chip

3.0

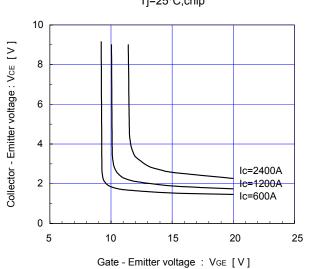
8V

5.0

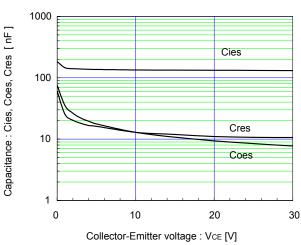
4.0



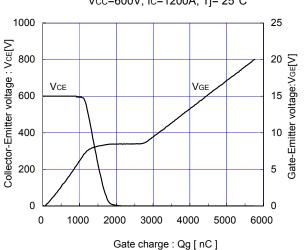
Collector-Emitter voltage vs. Gate-Emitter voltage (typ.) Tj=25°C,chip



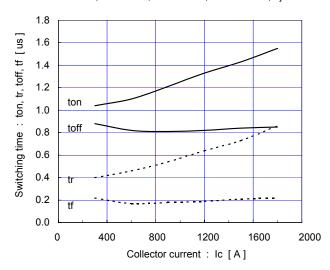
Capacitance vs. Collector-Emitter voltage (typ.) VGE=0V, f= 1MHz, Tj= 25°C



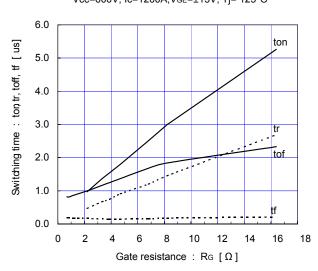
Dynamic Gate charge (typ.) Vcc=600V, Ic=1200A, Tj= 25°C



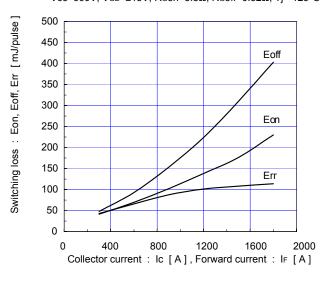
Switching time vs. Collector current (typ.) Vcc=600V, VgE= \pm 15V, Rgon=3.3 Ω , Rgoff=0.82 Ω , Tj= 125°C



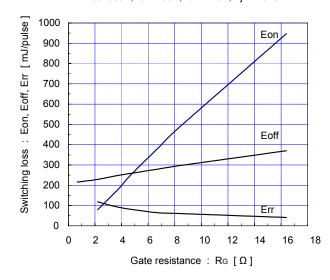
Switching time vs. Gate resistance (typ.) Vcc=600V, Ic=1200A,VcE=±15V, Tj= 125°C



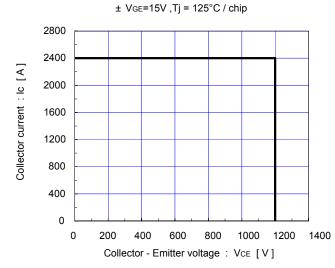
Switching loss vs. Collector current (typ.) Vcc=600V, VgE= \pm 15V, Rgon=3.3 Ω , Rgoff=0.82 Ω , Tj= 125°C



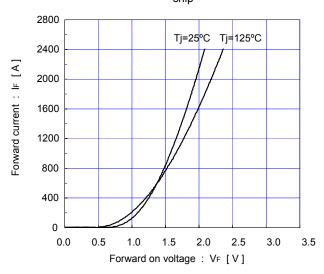
Switching loss vs. Gate resistance (typ.) Vcc=600V, Ic=1200A,VGE=±15V, Tj= 125°C



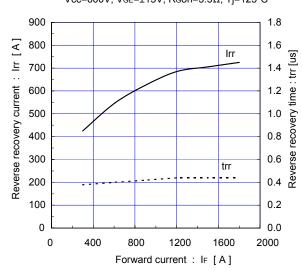
Reverse bias safe operating area (max.)



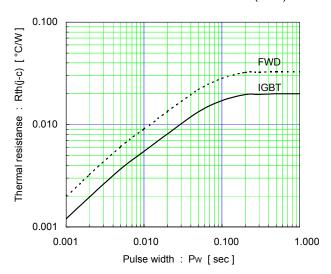
Forward current vs. Forward on voltage (typ.)



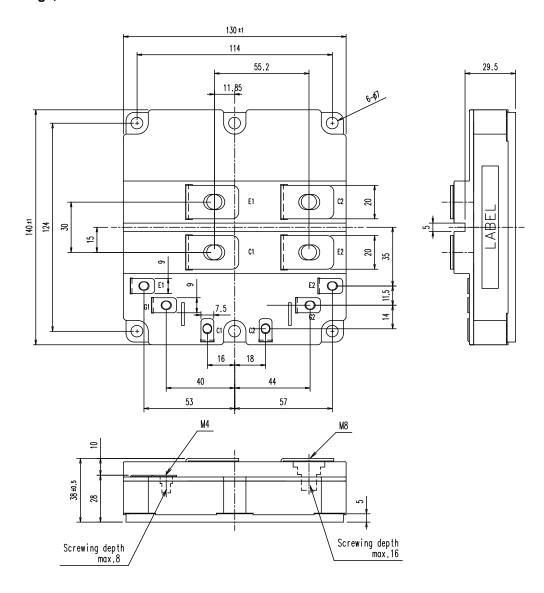
Reverse recovery characteristics (typ.) Vcc=600V, VgE= \pm 15V, Rgon= 3.3Ω , Tj= 125° C



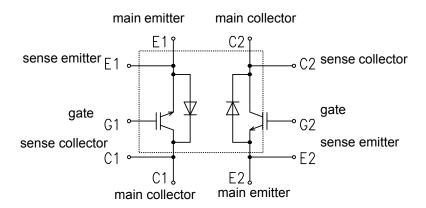
Transient thermal resistance (max.)



■ Outline Drawings, mm



■ Equivalent Circuit Schematic



http://www.fujielectric.com/products/semiconductor/

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